



UT2340

Power MOSFET

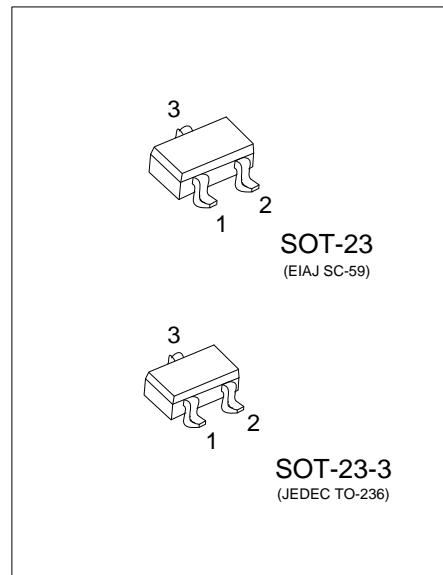
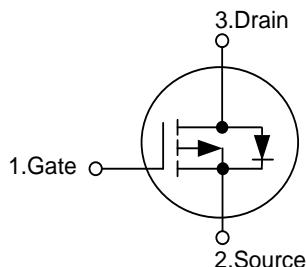
-4.2A, -20V P-CHANNEL ENHANCEMENT MODE

■ DESCRIPTION

The UTC UT2340 is P-Channel enhancement mode Power MOSFET, designed in serried ranks with fast switching speed, low on-resistance and favorable stabilization.

Used in commercial and industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

■ SYMBOL



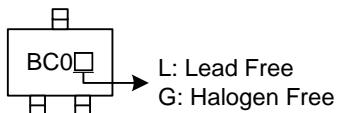
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UT2340L-AE2-R	UT2340G-AE2-R	SOT-23-3	G	S	D	Tape Reel
UT2340L-AE3-R	UT2340G-AE3-R	SOT-23	G	S	D	Tape Reel

Note: Pin Assignment: G: Gate S: Source D: Drain

UT2340G-AE2-R	(1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) AE2: SOT-23-3, AE3: SOT-23 (3) G: Halogen Free and Lead Free, L: Lead Free
---------------	--------------------------------------------------------	-------------------------------------------------------------------------------------------------------

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNITS
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current (Note 3) ($T_A=25^\circ\text{C}$)	I_D	-4.2	A
Pulsed Drain Current (Note 1, 2)	I_{DM}	-10	A
Power Dissipation	SOT-23-3	0.83	W
	SOT-23	1.38	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient (Note 3)	SOT-23-3	150	$^\circ\text{C}/\text{W}$
	SOT-23	90	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

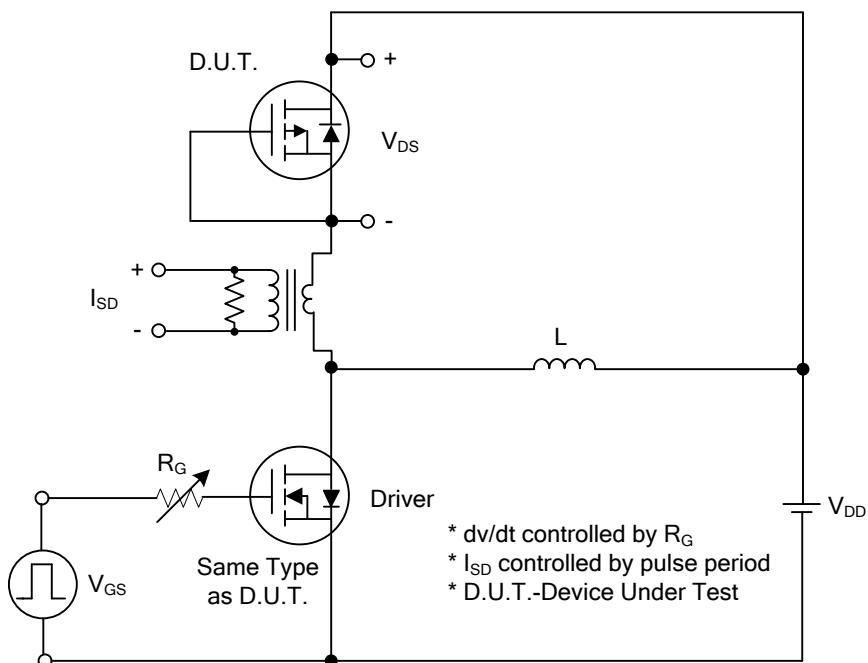
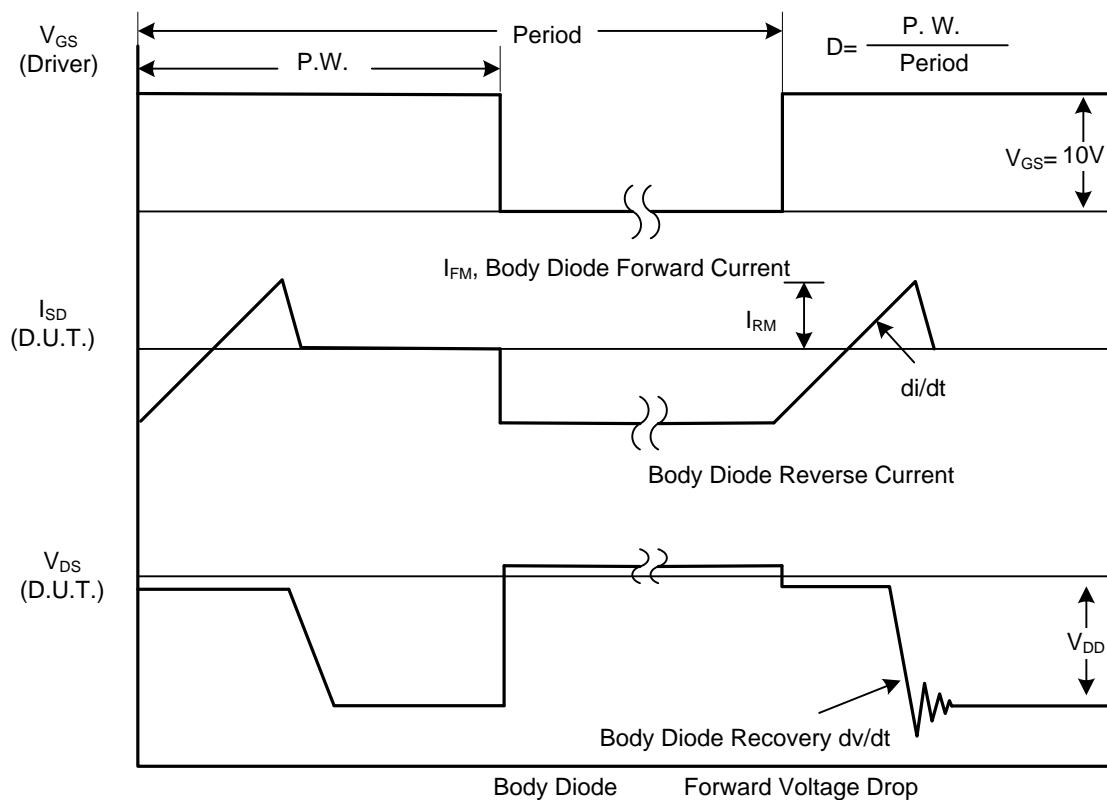
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{V}, I_D=-250\mu\text{A}$	-20			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-20\text{V}, V_{GS}=0\text{V}$			-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8\text{V}, V_{DS}=0\text{V}$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(\text{TH})}$	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.5		-1.2	V
Drain-Source On-State Resistance (Note 2)	$R_{DS(\text{ON})}$	$V_{GS}=-4.5\text{V}, I_D=-4.2\text{A}$			70	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}, I_D=-3.4\text{A}$			110	$\text{m}\Omega$
		$V_{GS}=-1.8\text{V}, I_D=-2.0\text{A}$			210	$\text{m}\Omega$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}			932		pF
Output Capacitance	C_{OSS}	$V_{GS}=0\text{V}, V_{DS}=-20\text{V}, f=1\text{MHz}$		100		pF
Reverse Transfer Capacitance	C_{RSS}			87		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 2)	Q_G	$V_{DS}=-4\text{V}, V_{GS}=-4.5\text{V}, I_D=-3.5\text{A}$		12.5		nC
Gate-Source Charge	Q_{GS}			2.5		nC
Gate-Drain Charge	Q_{GD}			1.8		nC
Turn-ON Delay Time (Note 2)	$t_{D(\text{ON})}$	$V_{DS}=-4\text{V}, V_{GS}=-4.5\text{V}, I_D=-1\text{A}, R_G=6\Omega, R_D=4\Omega$		10		ns
Turn-ON Rise Time	t_R			39		ns
Turn-OFF Delay Time	$t_{D(\text{OFF})}$			42		ns
Turn-OFF Fall Time	t_F			28		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				-4.2	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				-10	A
Drain-Source Diode Forward Voltage (Note 2)	V_{SD}	$V_{GS}=0\text{V}, I_S=-1.2\text{A}$			-1.2	V

Notes: 1. Pulse width limited by $T_{J(\text{MAX})}$

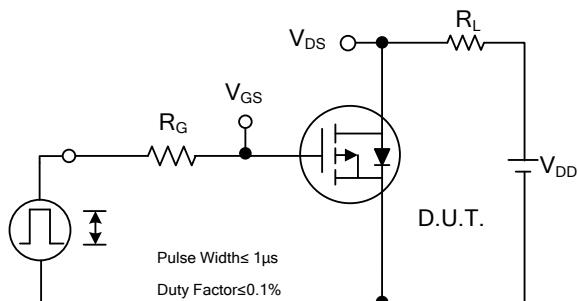
2. Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

3. Surface mounted on 1 in² copper pad of FR4 board; 270°C/W when mounted on min.

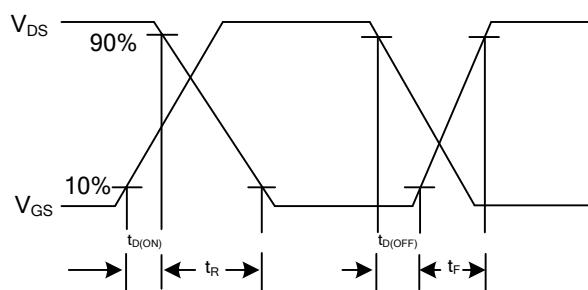
■ TEST CIRCUITS AND WAVEFORMS

Peak Diode Recovery dv/dt Test CircuitPeak Diode Recovery dv/dt Waveforms

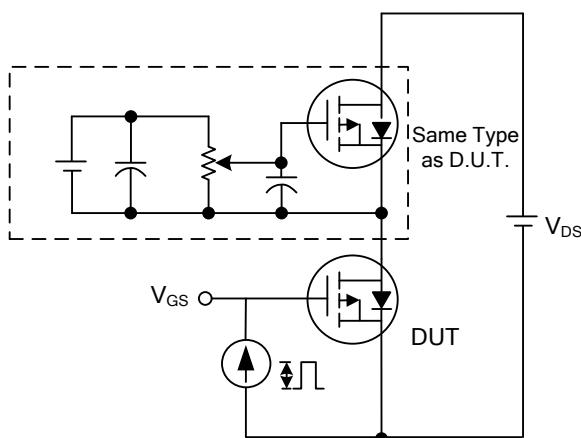
■ TEST CIRCUITS AND WAVEFORMS



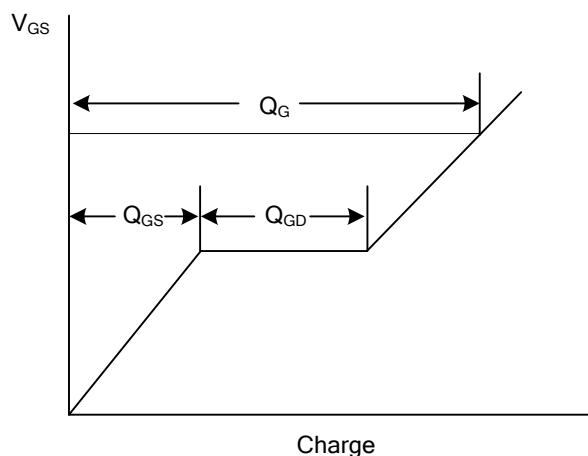
Switching Test Circuit



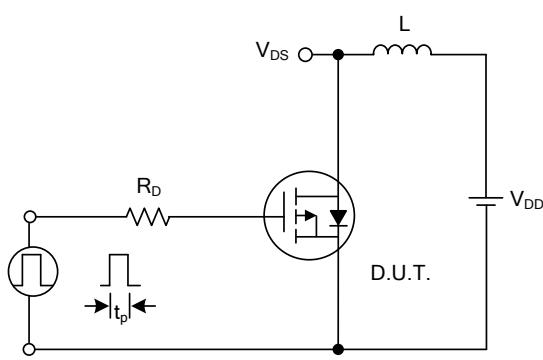
Switching Waveforms



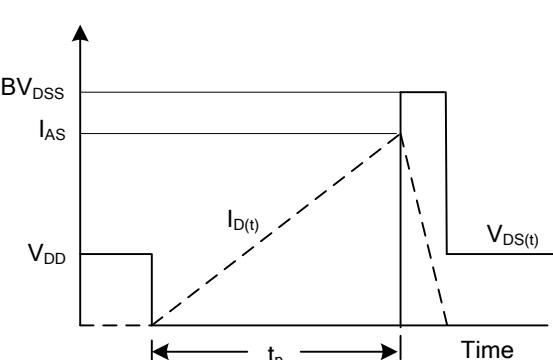
Gate Charge Test Circuit



Gate Charge Waveform

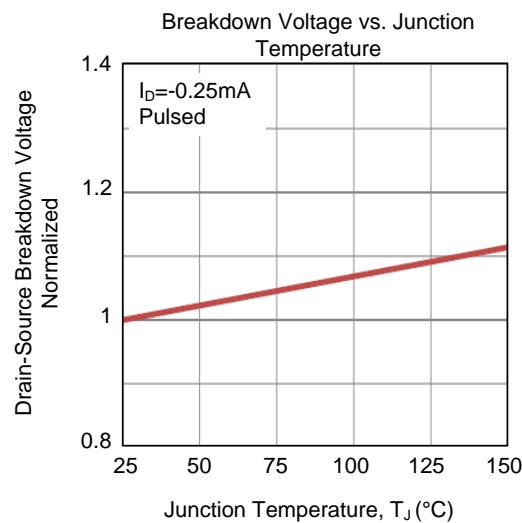
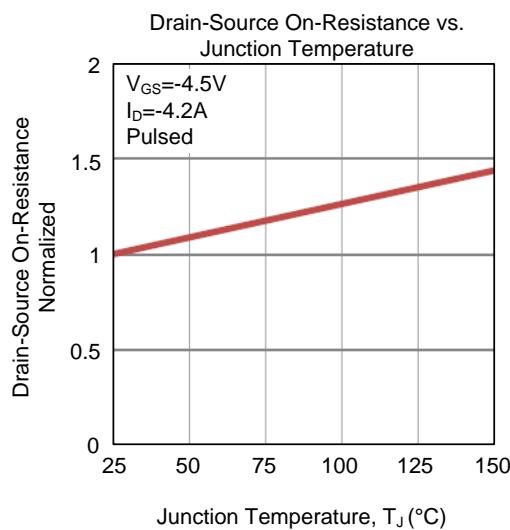
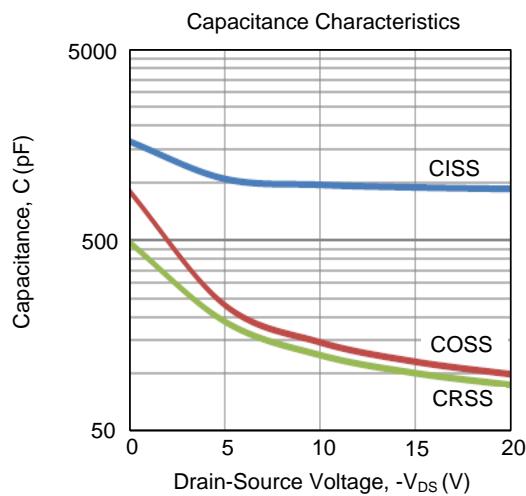
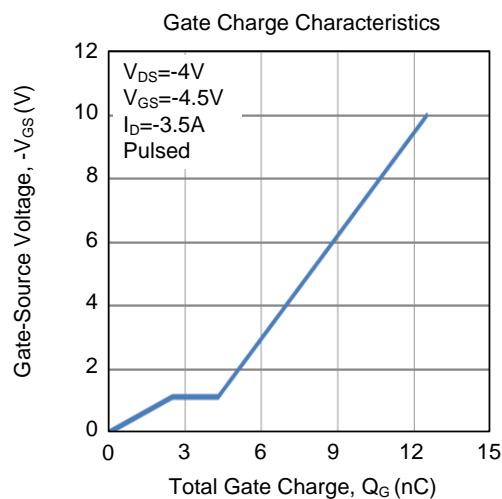
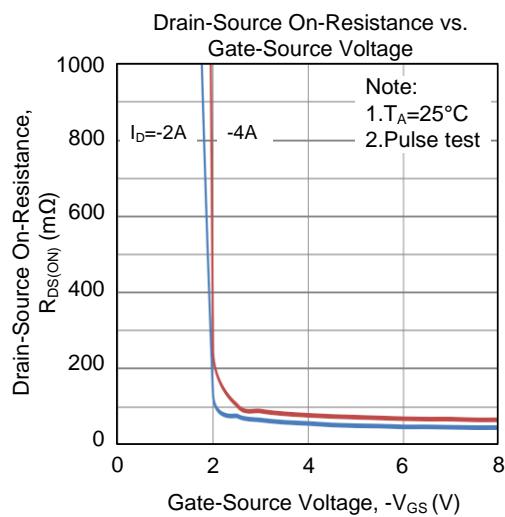
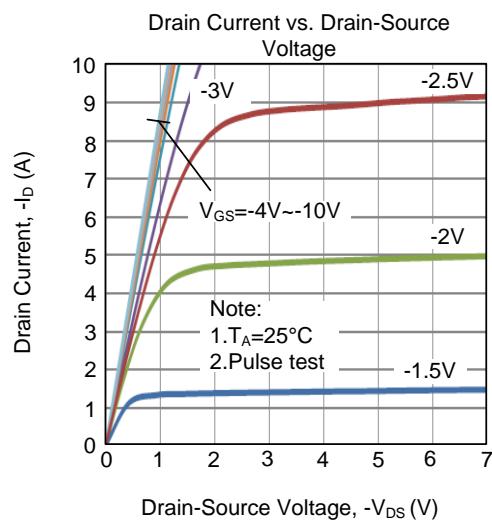


Unclamped Inductive Switching Test Circuit

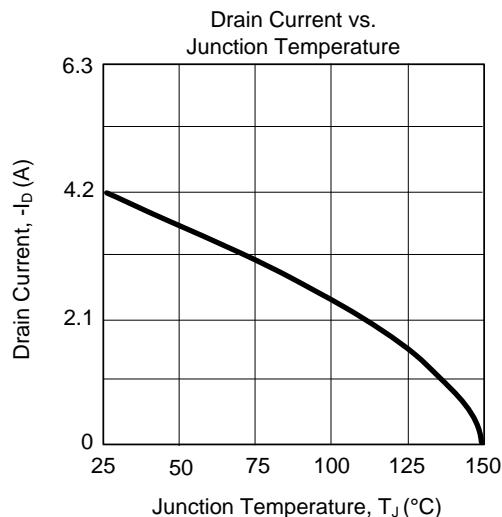
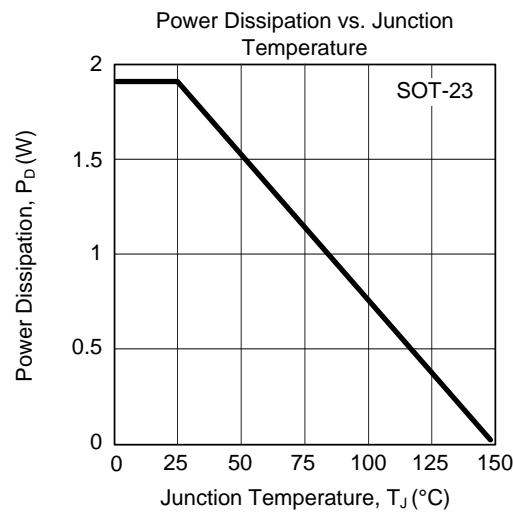
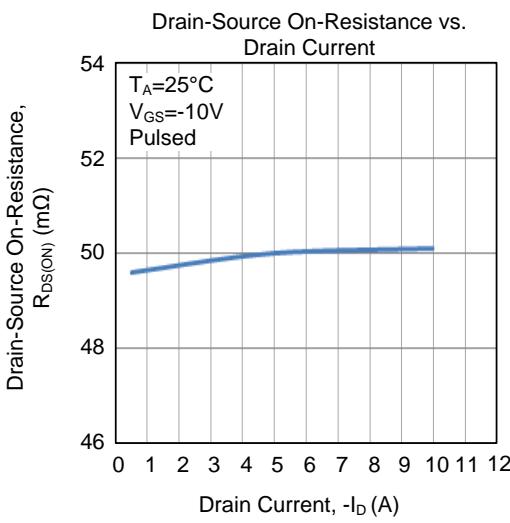
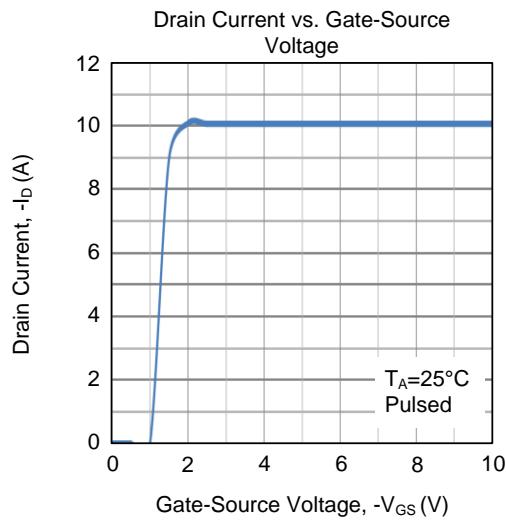
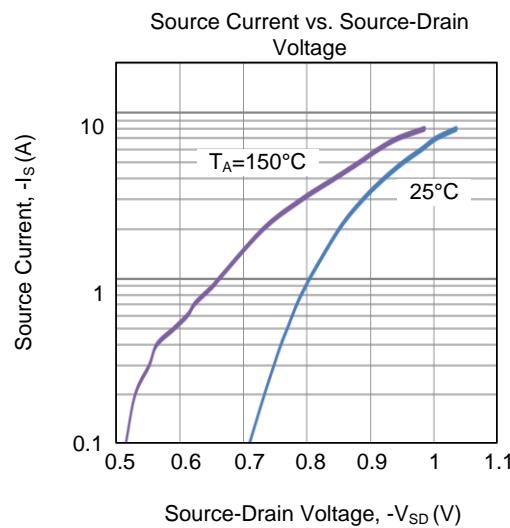
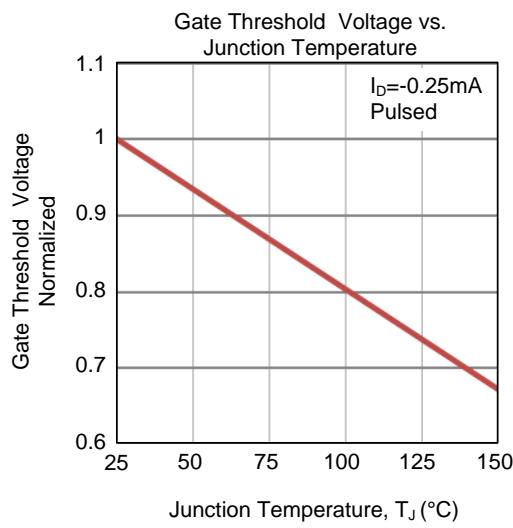


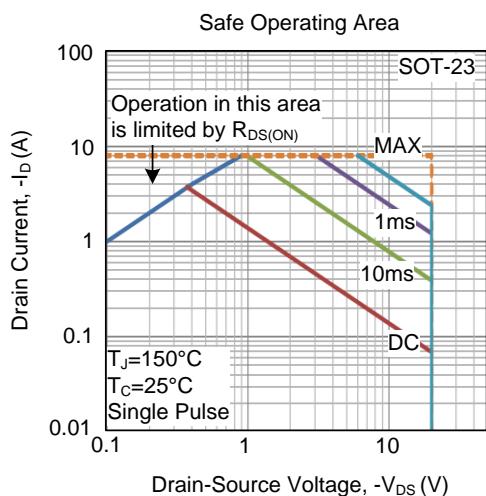
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.